

Silicon PNP Power Transistors

2SB953 2SB953A

DESCRIPTION

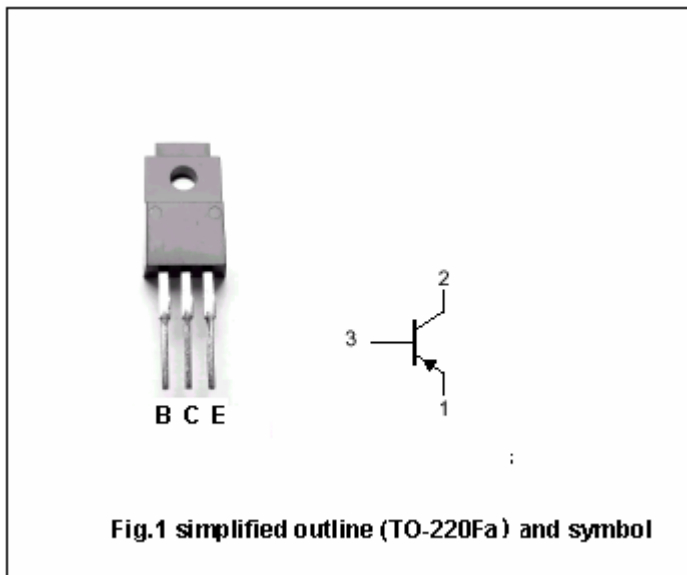
- With TO-220Fa package
- Complement to type 2SD1444/1444A
- High speed switching
- Low collector saturation voltage

APPLICATIONS

- For low-voltage switching

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2SB953	-40	V
		2SB953A	-50	
V _{CEO}	Collector-emitter voltage	2SB953	-20	V
		2SB953A	-40	
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-7	A
I _{CM}	Collector current-peak		-12	A
P _C	Collector power dissipation	T _a =25	2	W
		T _C =25	30	
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO}	Collector-emitter voltage	2SB953	I _C =-10mA; I _B =0	-20			V
		2SB953A		-40			
V _{CEsat}	Collector-emitter saturation voltage		I _C =-5A; I _B =-0.16A			-0.6	V
V _{BEsat}	Base-emitter saturation voltage		I _C =-5A; I _B =-0.16A			-1.5	V
I _{CBO}	Collector cut-off current	2SB953	V _{CB} =-40V; I _E =0			-50	μA
		2SB953A	V _{CB} =-50V; I _E =0				
I _{EBO}	Emitter cut-off current		V _{EB} =-5V; I _C =0			-50	μA
h _{FE-1}	DC current gain		I _C =-0.1A; V _{CE} =-2V	45			
h _{FE-2}	DC current gain		I _C =-2A; V _{CE} =-2V	90		260	
f _T	Transition frequency		I _C =-0.5A; V _{CE} =-10V, f=10MHz		150		MHz
C _{OB}	Collector output capacitance		f=1MHz; V _{CB} =-10V		140		pF

Switching times

t _{on}	Trun-on time			0.1		μs
t _s	Storage time	I _C =-2A I _{B1} =-66mA, I _{B2} =66mA		0.5		μs
t _f	Fall time			0.1		μs

◆ h_{FE-2} Classifications

Q	P
90-180	130-260

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PACKAGE OUTLINE

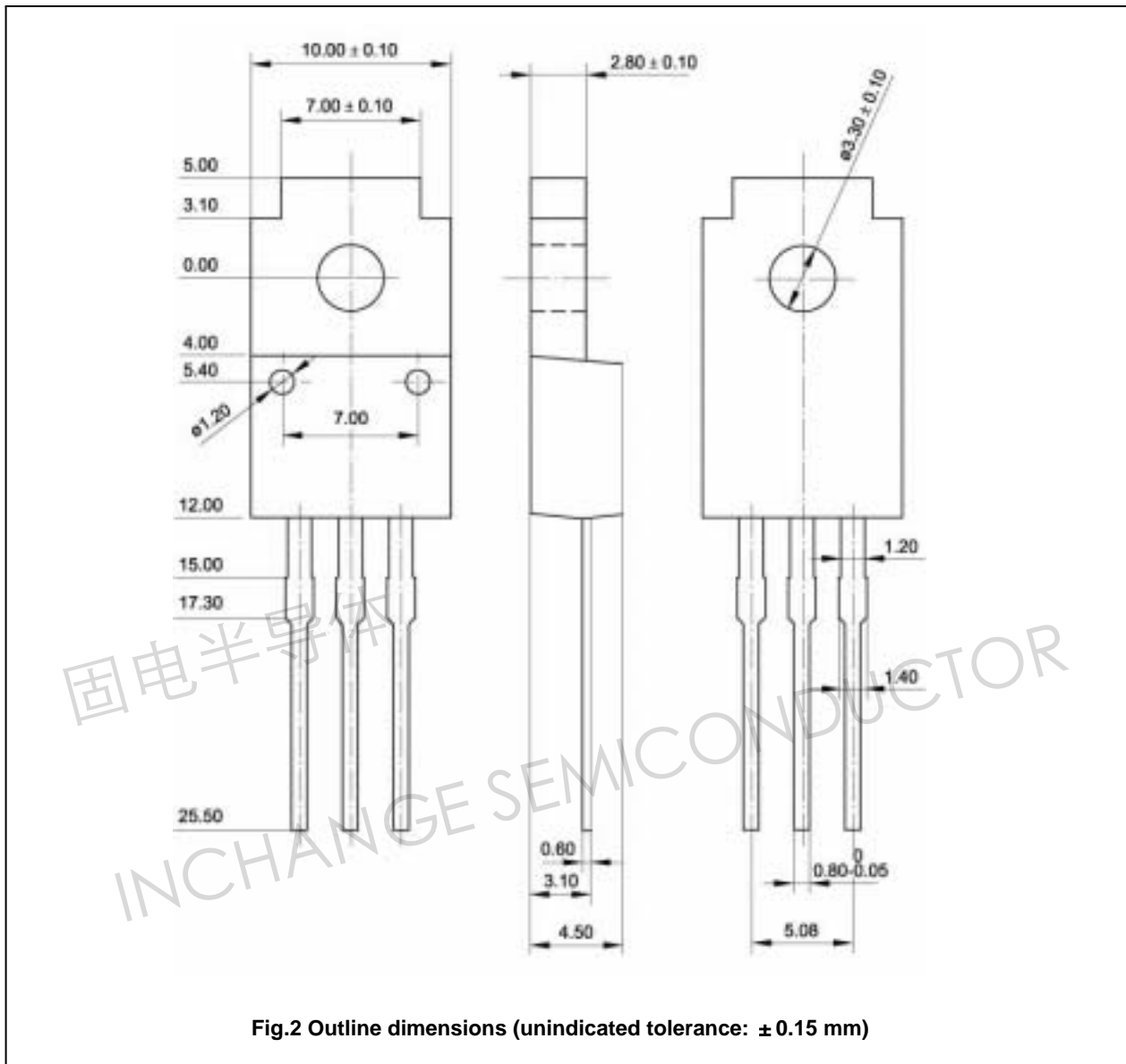


Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)

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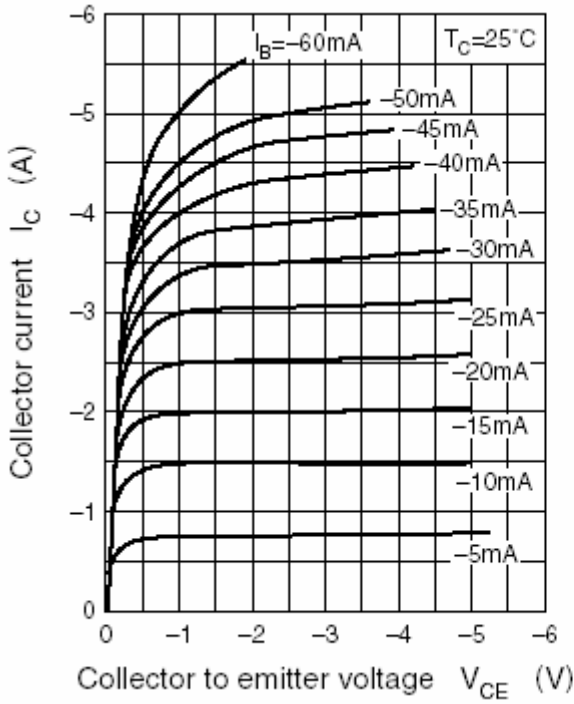


Fig.3 Static Characteristic

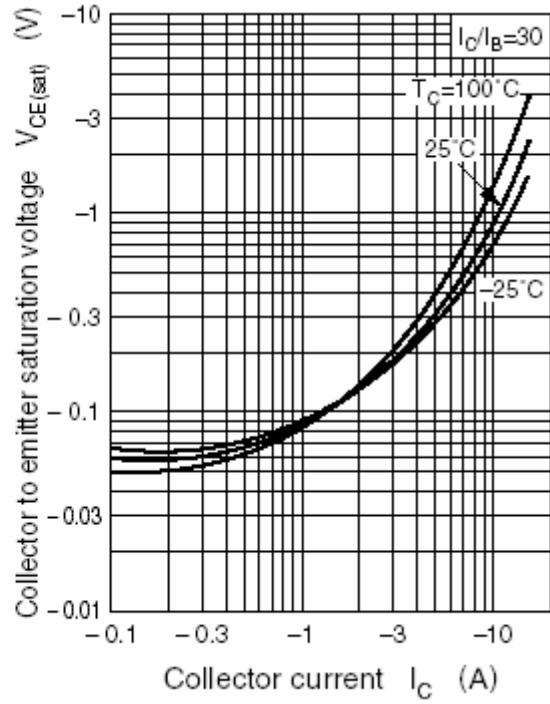


Fig.4 Collector-Emitter Saturation Voltage

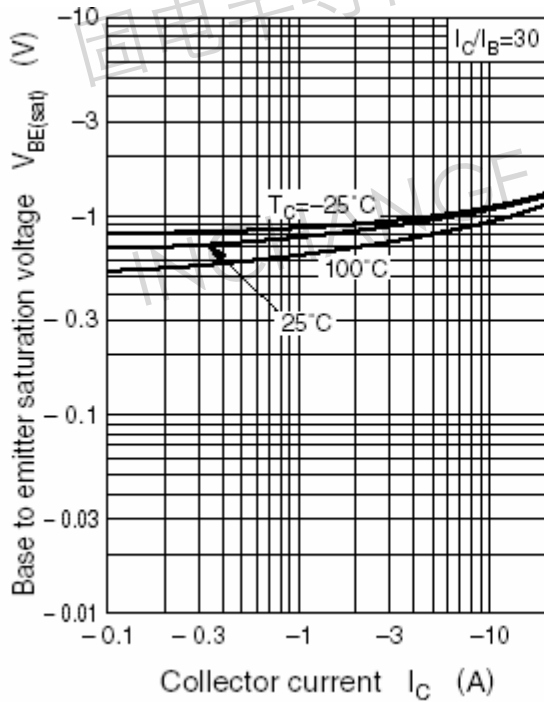


Fig.5 Base-Emitter Saturation Voltage

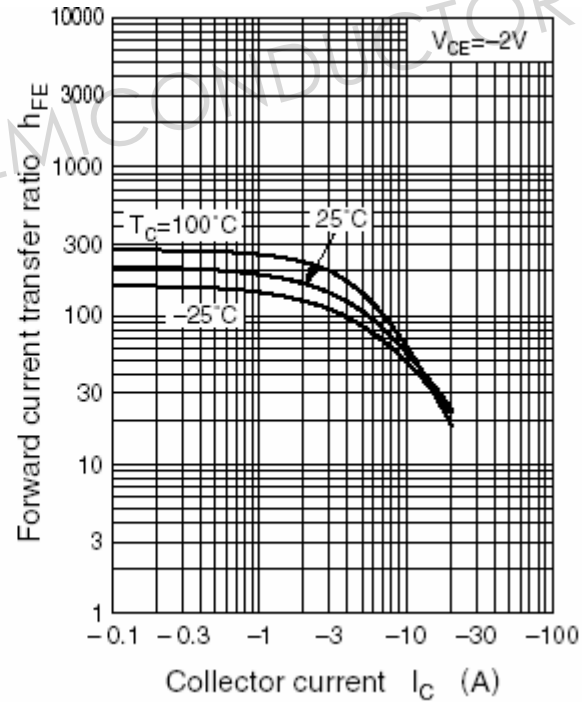


Fig.6 DC current Gain

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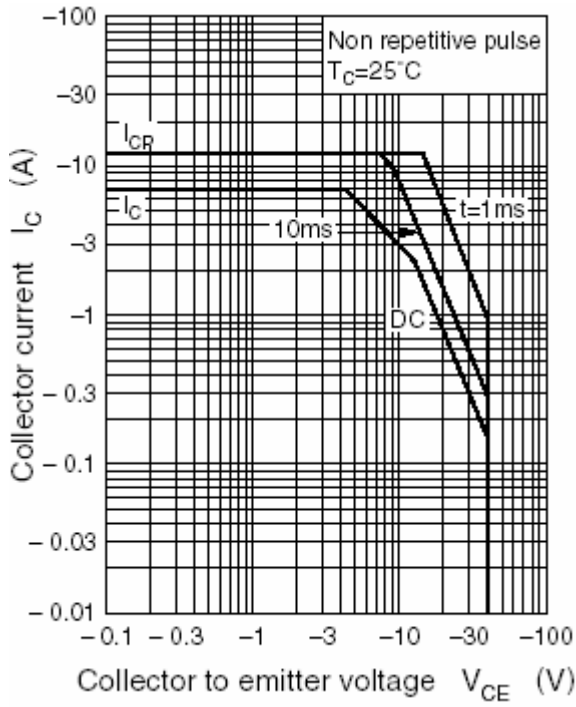


Fig.7 Safe Operating Area

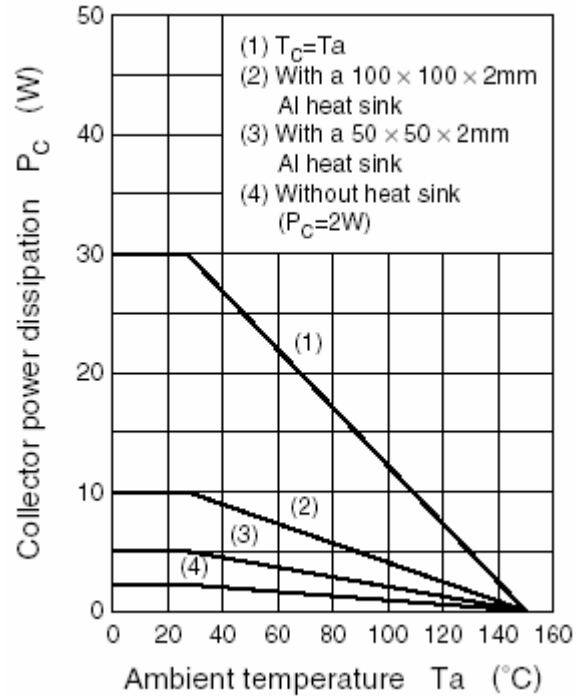


Fig.8 P_C - T_a Derating

固电半导体

INCHANGE SEMICONDUCTOR